Product data sheet

1. General description

NPN/NPN low V_{CEsat} transistor pair in a SOT457 (SC-74) Surface Mounted Device (SMD) plastic package.

PNP/PNP complement: PBSS5160DS

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · High collector current gain (hFE) at high IC
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- Dual low power switches (e.g. motors, fans)
- · Automotive applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	60	V	
I _C	collector current		[1]	-	-	1	Α	
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	2	Α	
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	200	250	mΩ	

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



60 V, 1 A NPN/NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 B2 E2
2	B1	base TR1	<u> </u>	
3	C2	collector TR2		(TR1 TR2)
4	E2	emitter TR2	<u>0</u>	
5	B2	base TR2	TSOP6 (SOT457)	
6	C1	collector TR1		sym020

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
PBSS4160DS	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4160DS	B8

60 V, 1 A NPN/NPN low VCEsat transistor

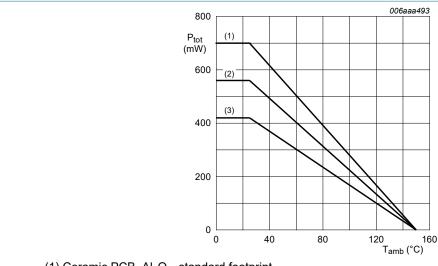
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or					
V _{CBO}	collector-base voltage	open emitter		-	80	V
V_{CEO}	collector-emitter voltage	open base		-	60	V
V_{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current		[1]	-	0.87	А
			[2]	-	1	Α
			[3]	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α
I _B	base current			-	300	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	290	mW
			[2]	-	370	mW
			[3]	-	450	mW
Per device			'			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	420	mW
			[2]	-	560	mW
			[3]	-	700	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

PBSS4160DS

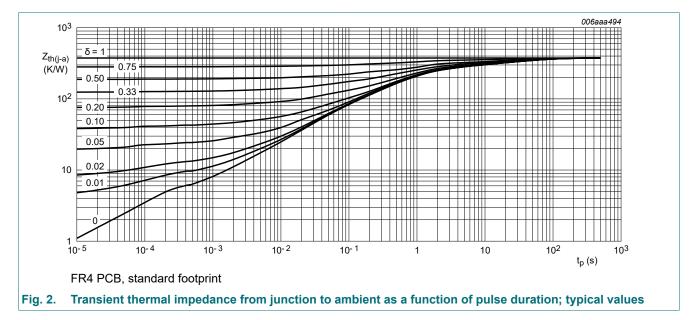
60 V, 1 A NPN/NPN low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
uily a)	thermal resistance from	in free air	[1]	-	-	431	K/W
	junction to ambient		[2]	-	-	338	K/W
			[3]	-	-	278	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	105	K/W
Per device			'	'	'	'	
R _{th(j-a)}		thermal resistance from in free air	[1]	-	-	298	K/W
	junction to ambient		[2]	-	-	223	K/W
			[3]	-	-	179	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



60 V, 1 A NPN/NPN low VCEsat transistor

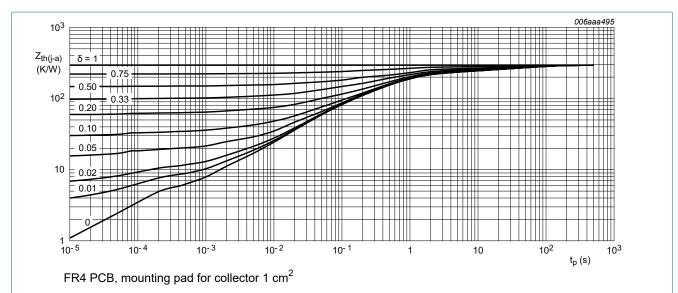


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

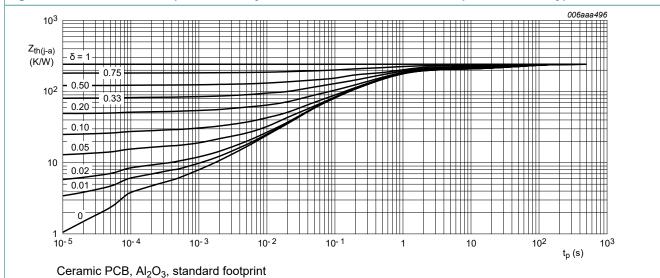


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 1 A NPN/NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor					
Ісво	collector-base cut-off	V _{CB} = 60 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 60 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
CES	collector-emitter cut-off current	V _{CE} = 60 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	250	500	-	
		V_{CE} = 5 V; I_{C} = 500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	420	-	
		V_{CE} = 5 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	100	180	-	
V _{CEsat} collector-emitter saturation voltage		I _C = 100 mA; I _B = 1 mA; T _{amb} = 25 °C	-	90	110	mV
	saturation voltage	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	115	140	mV
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$	-	200	250	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	200	250	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.95	1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 5 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	0.82	0.9	V
d	delay time	I _C = 0.5 A; I _{Bon} = 25 mA; I _{Boff} = -25 mA;	-	11	-	ns
r	rise time	T _{amb} = 25 °C	-	78	-	ns
on	turn-on time		-	90	-	ns
·s	storage time		-	340	-	ns
f	fall time		-	160	-	ns
off	turn-off time		-	500	-	ns
ŤΤ	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	150	220	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	-	5.5	10	pF

60 V, 1 A NPN/NPN low VCEsat transistor

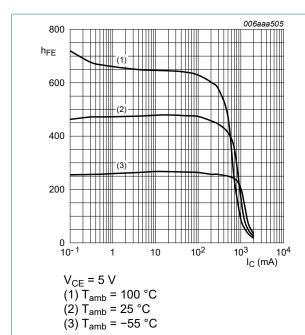


Fig. 5. DC current gain as a function of collector current; typical values

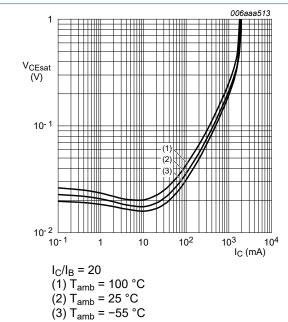


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

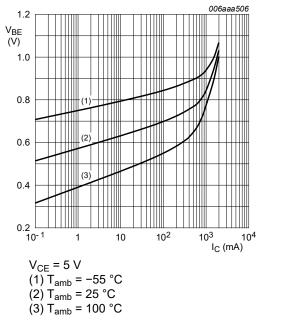
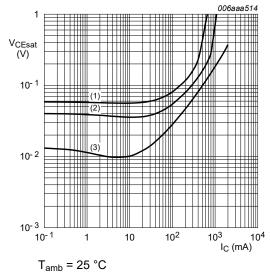


Fig. 6. Base-emitter voltage as a function of collector current; typical values



(1) $I_C/I_B = 100$ (2) $I_C/I_B = 50$ (3) $I_C/I_B = 10$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

60 V, 1 A NPN/NPN low VCEsat transistor

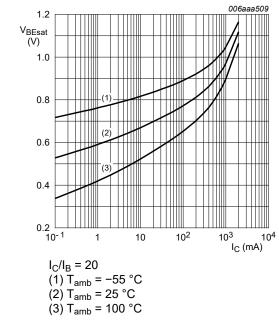


Fig. 9. collector current; typical values

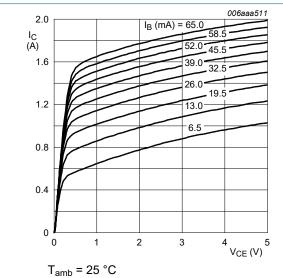
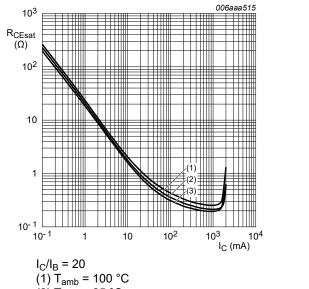
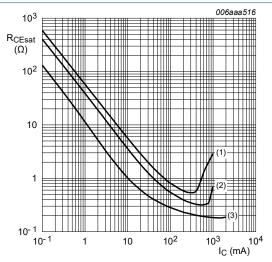


Fig. 11. Collector current as a function of collectoremitter voltage; typical values



(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

Base-emitter saturation voltage as a function of Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



 T_{amb} = 25 °C (1) $I_C/I_B = 100$ (2) $I_{\rm C}/I_{\rm B} = 50$ (3) $I_C/I_B = 10$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 1 A NPN/NPN low VCEsat transistor

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

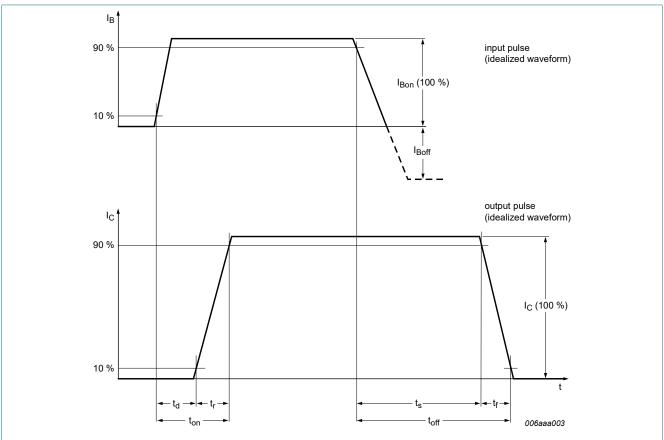
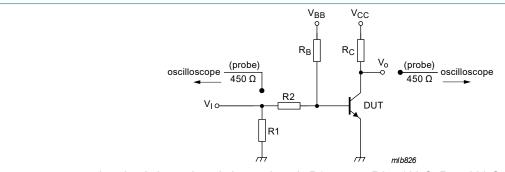


Fig. 13. Transistor switching time definition

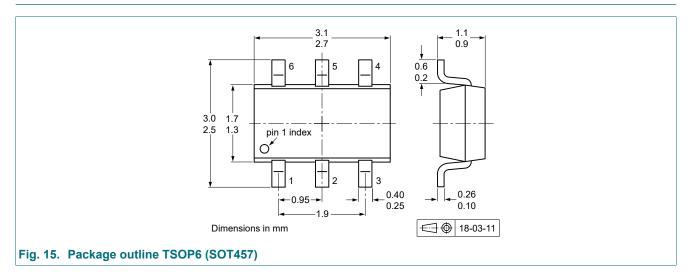


 I_C = 0.5 A; I_{Bon} = 25 mA; I_{Boff} = -25 mA; R1 = open; R2 = 100 Ω ; R_B = 300 Ω ; R_C = 20 Ω

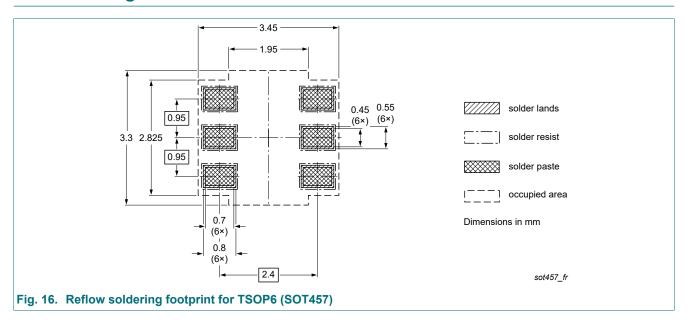
Fig. 14. Test circuit for switching times

60 V, 1 A NPN/NPN low VCEsat transistor

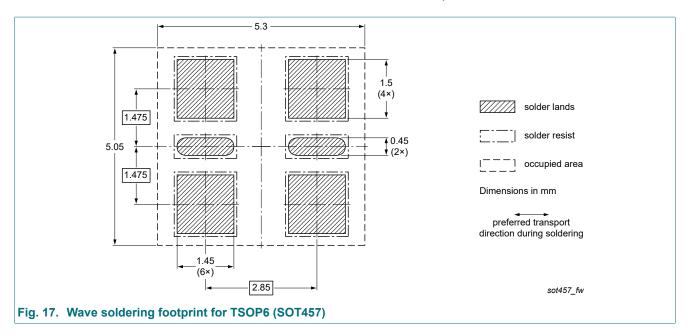
12. Package outline



13. Soldering



60 V, 1 A NPN/NPN low VCEsat transistor



60 V, 1 A NPN/NPN low VCEsat transistor

14. Revision history

Table 8. Revision history

Table 6. Revision ins	stor y			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160DS v.5	20230921	Product data sheet	-	PBSS4160DS_4
Modifications:	Nexperia. • Legal texts have	this data sheet has been rede we been adapted to the new c ng information" removed.	.,	
PBSS4160DS_4	20091211	Product data sheet	-	PBSS4160DS_3
PBSS4160DS_3	20060209	Product data sheet	-	PBSS4160DS_2
PBSS4160DS_2	20050627	Product data sheet	-	PBSS4160DS_1
PBSS4160DS_1	20040426	Objective data sheet	-	-

60 V, 1 A NPN/NPN low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PBSS4160DS

60 V, 1 A NPN/NPN low VCEsat transistor

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10	. Characteristics	6
11.	. Test information	9
12	. Package outline	10
13	. Soldering	10
	. Revision history	
	. Legal information	

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